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1 Plasmo-electronic properties of self-assembled gold

2 **nanoparticles: impedance spectroscopy experiments**

3 combined with numerical simulations

4 LOUIS MERLE¹, ADNEN MLAYAH^{2,3} AND JÉRÉMIE GRISOLIA^{*1}

5 ¹LPCNO, Université de Toulouse, INSA, CNRS, UPS, 135 Avenue de Rangueil, Toulouse 31077, France

6 ² CEMES, Université de Toulouse, CEMES-CNRS, 29 rue Jeanne Marvig, Toulouse 31055, France

7 ³ LAAS, Université de Toulouse, CNRS, UPS, 7 avenue du Colonel Roche, Toulouse 31031, France

8 *<u>jeremie.grisolia@insa-toulouse.fr</u>

9 Abstract: Plasmo-electronics is a fast developing field driven by the combination of charge transport and surface plasmons in metal nanostructures. In this paper, we report 10 11 on theoretical and experimental investigations of the plasmoelectronic properties of self-assembled monolayers of colloidal gold nanoparticles. A local plasmonic-12 electronic nano-junction is introduced, as the fundamental component of a meso-scale 13 14 electrical network, and serves as the beginning point for the development of a multiscale modeling strategy. The Inter-particle charge tunneling and accumulation account 15 16 for the dynamical charge transport; the plasmonic properties are implemented at the nanoscale using electro-dynamic calculations based on the discrete dipole 17 18 approximation (DDA) method. The electric characteristics of the macroscopic nanoparticle network are calculated using a numerical resolution of the current-bias 19 equations based on Kirchhoff's laws. Disorder effects due to size and position 20 21 fluctuations of the nanoparticles within the network as well as dislocations and point defects in their spatial arrangement are taken into account. The effects of light 22 excitation intensity and wavelength on the nano-junction photo-conductance and on 23 24 the macroscopic photo-resistance of the nanoparticle network are addressed. In particular, plasmo-electronic conduction paths are extracted from the coupled DDA-25 26 Kirchhoff numerical simulations and their statistical distribution is investigated as well 27 as their dependence on path length. The theoretical results are compared with 28 impedance spectroscopy measurements performed under optical excitation. We found 29 a good agreement between the predicted impedance Nyquist plots and resonance properties, and the measurements. In particular, we were able to estimate the surface 30 plasmon assisted photo-electric conversion coefficient involving first neighbor 31 32 nanoparticles. We found that the photo-conductance of a single nano-junction formed by a dimer of nearly touching nanoparticles is around 18 nS.W⁻¹.cm² under resonant 33 plasmonic excitation. The presented work provides insight into the photo-induced 34 charge transport in self-assembled nanoparticle networks and opens the route to novel 35 applications in the field of plasmo-electronics. 36

37

38 1. Introduction

The driving force behind the development of plasmoelectronics is the link between charge transport and surface plasmons in metal nanostructures [1]–[5]. It has been shown that charging metal nanoparticles can alter their plasmonic response, and vice versa, that surface plasmon excitation of a nanoparticle assembly can modify 43 macroscopic fluxes of charges [6]-[8]. In particular, a rise or a decrease of conductance, under optical excitation tuned to the nanoparticles surface plasmon 44 45 resonance, has been pointed out [6], [9], [10]. In this situation, it had been found that negatively charged ligands act as charge traps lowering the free carrier density and 46 resulting in a negative photo-conductance. However, since positive photo-conductance 47 with charged ligands has also been discovered, this view has been vividly contested in 48 the literature [11]–[13]. Additionally, the ligand molecules' ability to impose a tunnel 49 50 barrier between two adjacent nanoparticles, regardless of their charge state, determines whether the macroscopic electrical properties of the nanoparticle assemblies behave 51 like a metal or an insulator [14]. Moreover, despite the fact that these NPs assemblies 52 are granular in form, that is, made up of conductive and insulating regions, most 53 published investigations to date have concentrated on the analysis of the resistance 54 55 properties, only [6] [9]-[11], [13]-[21]. The capacitive properties have only been briefly discussed in a few papers [12], [22]. In this respect, we have previously 56 demonstrated [12], that both resistive and capacitive characteristics are complementary 57 and can be used to further understanding the charge transport properties of self-58 59 assembled nanoparticle networks. Indeed, the macroscopic electrical characteristics of 60 self-assembled NPs were experimentally investigated using impedance spectroscopy 61 and were modeled using a bottom-up approach in which local interconnected nano-62 junction circuits are introduced as building blocks of a macroscopic electrical circuit to describe the charge transport properties of the nanoparticle self-assembly (Figure 63 2). However, the photo-induced effects were accounted only at the macroscopic level, 64 which provided a first attempt to the modeling of the plasmonic induced photo-65 66 conductance in self-assembled gold nanoparticle networks and the macroscopic conversion efficiency of the electromagnetic energy into electric current has been 67 estimated. 68

69 In this paper, we focus on the conversion of light into electrical current in selfassembled plasmonic NPs networks. This phenomenon is quite complex and involves 70 71 several interaction steps between elementary excitations (plasmons, electron-hole pairs, phonons), but it is still poorly understood in terms of the relationship between 72 73 local opto-electronic properties at the nanoparticle scale and the macroscopic electrical 74 characteristics of the nanoparticle self-assembly. We demonstrate that utilizing 75 numerical simulations combined with impedance spectroscopy measurements, it is 76 possible to connect the macro-scopic and the nano-scopic opto-electronic properties of metal NPs assemblies. To account for the photo-induced charge carriers generation 77 78 and transport, a local positive photoconductance is introduced at the nano-scale. The 79 current passing through the nanoparticle assembly, including its optical component, is determined by implementing electrodynamic calculations into Kirchhoff's laws. This 80 method enables the definition of a macroscopic photo-conductance. The theoretical 81 results are discussed in terms of plasmo-electronic properties of the nanoparticle self-82 assembly and are compared to impedance spectroscopy measurements carried out 83 under optical excitation of the plasmonic resonance of the nanoparticles. In this way 84 we are able to assess the efficiency of the plasmonic assisted light-to-current 85 conversion at the nanoscopic level. Such a physical quantity is very difficult to 86 determine including in near-field based optical spectroscopy techniques. 87

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89 2. Experimental and numerical details:

91 2.1 - Chemical synthesis and sample preparation:

92 The chemical synthesis procedure is described in details elsewhere [22], [23]. Briefly, gold nanoparticles stabilized with dodecanethiol (C_{12}) organic ligands (1.2nm 93 94 length) were synthesized with the protocol described by Zheng et al. [24]. The average 95 size of the nanoparticles is $7 \pm 0.7 nm$ determined by transmission electronic microscopy (TEM). On the other hand, interdigitated gold electrodes were patterned 96 on a 125 µm thick polyimide (Upilex) film using laser lithography and a 50 nm thick 97 Au layer was deposited over the entire surface by IBS-E ion beam sputtering. After 98 99 lift-off, a 1 mm² device consisting in 50 pairs of inter-digitated 5 µm wide electrodes separated by 5 µm is obtained and connected to external gold electrodes (Figure 1a). 100 Gold NPs from the colloidal solution were deposited on the device using the ethylene 101 102 glycol drop casting method described elsewhere (Figure 1b) [22]. This technique allows to obtain a quite uniform and homogeneous monolayer of self-assembled 103 104 nanoparticles well ordered in a hexagonal lattice network on a macroscopic scale (1 105 mm^2) (Figure 1).



Figure 1 : (a) Optical image showing a 1mmx1mm device formed by 50 interdigited electrodes (b) Scanning electron microscopy (SEM) image of the interdigitated electrodes on top of which the NP assembly is formed, (c) High resolution SEM image of the active area showing a monolayer of 7 nm gold nanoparticles self-assembled in a hexagonal lattice network, as attested by the electron diffraction pattern in the inset.

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112 **2.2** - Impedance spectroscopy under optical excitation:

113 Impedance spectroscopy measurements were performed at room temperature 114 using a Keysight impedance analyzer EA4990A, in the 20Hz-5MHz frequency range 115 with a 500mV AC voltage. The set-up is equipped with an optical fiber located above 116 the sample which allows to shine laser light on the 1mm² entire active area (Figure 1a). 117 The optical fiber is connected to three laser diodes, operating at $\lambda = 405$, 532 and 640 118 nm wavelengths and up to W/cm² intensity.

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120 3. Plasmoelectronic modeling:

121 The approach developed in this work is based on numerical simulations of the 122 dynamical charge transport properties of a network composed of inter-connected 123 electric nano-circuits building blocks (Figure 2).

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Figure 2: (a) Transmission Electron Microscopy image of a ca. 220nm x 150nm region of the NP assembly with schematic contact electrodes, (b) electrical circuit formed by parallel resistance R, capacitor C and photo-resistance G_{photo}^{-1} describing the charge transport across the network formed by the inter-connected nano-junctions (c). Each nano-junction, formed by a pair of first neighbor nanoparticles, consists in parallel inter-particle tunneling resistance R_{ij} capacitor C_{ij} and photo-resistance $g_{ij_choto}^{-1}$.

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131 Each nano-junction is an electrical connexion between first neighbor 132 nanoparticles (labeled i and j) and consists in parallel inter-particle resistance R_{ij} , capacitor C_{ij} and photo-resistance $g_{ij_photo}^{-1}$ (Figure 2c). Calculations were performed 133 for a single layer of spherical gold NPs. The sizes and positions of the nanoparticles, 134 as well as the inter-particle gap distances were extracted from a 100 nm x 100 nm area 135 136 of the transmission electron microscopy (TEM) images (Figure 2a). The histogram of 137 interparticle distances in Figure ESI 1b shows that the average inter-particle gap 138 separation is around 2.8 nm which is slightly larger than twice the dodecanethiol 139 molecule length (1.2 nm). This indicates that disorder due to size and position fluctuations, to point defects (nanoparticle vacancies) and to dislocations and misfits 140 141 in the nanoparticle network are present. Figure ESI 1a depicts the 100 nm x 100 nm 142 nanoparticle region that serves as our model network for the computer simulations. In 143 this way, the actual spatial arrangement of the nanoparticles are taken into account in 144 the calculations and in the comparison with the experimental data.

145 Each (i,j) pair of nanoparticles located at positions (r_i, r_j) of the 2D network 146 gives rise to a parallel electrical nano-junction (Figure 2c) with admittance:

147 Eq. 1
$$\chi_{ij} = 1/R_{ij} + g_{ij_photo} + jC_{ij}\alpha$$

148 As shown in previous works [11], [14], [25], the quantum tunnelling resistance 149 R_{ij} between first neighbour nanoparticles is given by:

150 Eq. 2 $R_{ij} = R_0 \cdot e^{\xi(V_{ij},T)}$

where R_0 is the inter-particle tunnelling resistance at the touching limit, *i.e.* for vanishing inter-particle gap distance l_{ij} , ξ accounts for the charge tunnelling and for the Coulomb blockade effects and is given by ([11], [14], [25], [25]):

154
$$Eq. \ 3\xi = \beta l_{ij} - ln\left(g(E_c, T, V_{ij})\right)$$
 with $g(E_c, T, V_{ij}) = \frac{1}{eV_{ij}} \left(-\frac{E_c - eV_{ij}}{1 - e^{(E_c - eV_{ij})/k_BT}}\right)$

 $\frac{E_C + eV_{ij}}{1 - e^{\left(E_C + eV_{ij}\right)/k_BT}}\right)$ 155

Where β is the tunnelling decay constant, E_C is the Coulomb charging energy, T the 156 temperature and V_{ij} is the voltage between first neighbour nanoparticles *i* and *j*. In the 157 following we use $\beta = 5 \text{ nm}^{-1}$ and $E_C = 50 \text{meV}$ ([11], [13]) to describe the tunneling 158 resistance in the absence of optical excitation. 159

It is worth noting that the bias voltage applied to the nanoparticle network is of the 160 order of volts leading to inter-particle voltage V_{ij} very small compared to Ec/e ~ 50mV. 161 In addition $E_C > k_BT$ at room temperature. Using these two statements, Eq. 3 can be 162 163 approximated by [27]:

164 Eq. 4
$$\xi \approx \beta l_{ij} + \frac{L_c}{k_p}$$

 $L_{4'}$, $\zeta \sim \rho \iota_{ij} + \zeta / k_B T$ Assuming spherical nanoparticles, the inter-particle capacitor C_{ij} is given by [22], 165

166 [26]:

167 Eq. 5
$$C_{ij} = \pi \varepsilon d_{ij} \ln(1 + d_{ij}/l_{ij})$$

168 Where $\bar{d}_{ij} = (d_i + d_j)/2$ is the mean diameter of the *i* and *j* nanoparticles and ε is the permittivity of the surrounding medium (*i.e.* of the ligand molecules in our case). 169

170 As shown experimentally by Mangold et al. [10], [17], Gauvin et al. [28], the macroscopic photo-conductance increases linearly with increasing laser intensity for 171 low laser irradiation (below 7kW/cm²). This is confirmed in our investigated 172 nanoparticle networks as shown in Figure ESI 2. Based on this experimental finding, 173 we introduce a local nanoscopic photoconductance: 174

 $g_{ij_photo}(\lambda) = k_{ij}(\lambda) \cdot I_{ij}(\lambda) \cdot e^{-E_C/k_BT}$ 175 Eq. 6

Where $k_{ii}(\lambda)$ is a wavelength dependent local photo-conductance efficiency involving 176 177 first neighbor nanoparticles and the surrounding ligands molecules. $I_{ij}(\lambda) =$ $F_{ij}^{2}(\lambda) I_{0}$ is the local light intensity and $F_{ij}(\lambda) = |E_{ij}(\lambda)/E_{0}|$ is the electric field 178 enhancement factor which accounts for the plasmonic resonance; $I_0 = |E_0|^2$ is the 179 180 incident optical intensity.

In our approach, the light-to-current conversion mechanism is treated globally, 181 *i.e.* as due to both the nanoparticle and its surrounding medium; indeed, the ligand 182 183 molecules may also absorb light through HOMO-to-LUMO transitions and may thus 184 participate to the photo-generation of electron-hole pairs. Therefore, we assume that $F_{ii}(\lambda)$ is the electric field enhancement factor in the gap region between i and j 185 nanoparticles. The photo-generated charges flow across the nanoparticle network 186 owing to quantum tunneling between first neighbor nanoparticles. The photo-187 conductance efficiency $k_{ii}(\lambda)$ depends on the optical wavelength because the tunneling 188 189 process involves high energy photo-excited states (see Figure ESI 3), the so-called hot charge carriers. Therefore, we make the assumption that $k_{ij}(\lambda)$ takes the form : 190

191 Eq. 7
$$k_{ij}(\lambda) = k_0(\lambda). e^{-\beta(\lambda).l_i}$$

Where $k_0(\lambda)$ is a wavelength-dependent photo-conductance efficiency in 192 193 Siemens per unit of light intensity, which accounts for the photo-generation charge carriers at vanishing gap distance between two nanoparticles; and the exponential term 194 describes their interparticle tunneling; $\beta_{hot}(\lambda) = \sqrt{2.m.(V_b - E(\lambda))/\hbar})$ is the wave 195 vector of the photo-generated hot electrons, in which, m = 0.28.m₀ is the carriers 196

197 electron effective mass [29], $E(\lambda)$ is the photon energy and $V_b = 4.16$ eV is the energy 198 barrier height [29]. For example, at $\lambda = 532$ nm, $\beta_{hot} = 3.66$ nm⁻¹ and is smaller than 199 $\beta = 5$ nm⁻¹ which conveys the idea that hot carriers can tunnel over larger distances 100 than thermalized carriers (Figure ESI 3).

201 Calculations based on the Discrete Dipole Approximation (DDA) [30], [31] 202 were performed in order to determine the plasmonic field enhancement $F_{ij}(\lambda)$. The 203 nanoparticle self-assembly model is the 100 nmx100 nm area shown in Figure ESI 1a. 204 The medium surrounding each nanoparticle is dodecanethiol (with optical index 205 n=1.46).

Figure 3 shows maps of $F_{ii}(\lambda)$ calculated at three optical excitation wavelengths 206 207 around the plasmonic resonance. These maps show that the electro-magnetic 208 interactions between the NPs give rise to plasmonic hot spots in the gap regions between the nanoparticles. For the calculation of the local field intensity in Eq. 6, we 209 consider the intensity enhancement $\langle F_{ij}^2(\lambda) \rangle$ averaged over the gap distance between 210 first neighbor nanoparticles (Figure 3d). $\langle F_{ii}^2(\lambda) \rangle$ is around two orders of magnitudes 211 for a 1 nm interparticle distance and decreases with increasing l_{ii} (Figure 3e) which 212 confirm the origin of the plasmonic resonance as due to the near-field interaction 213 214 between first neighbor nanoparticles.



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Figure 3 : Electric field intensity enhancement $F_{ij}(\lambda) = |E_{ij}(\lambda)/E_0|$ calculated using DDA simulations performed on a 100 nm x 100 nm nanoparticle assembly shown in Figure ESI 1a. Maps of F_{ij}^2 calculated around the surface plasmon resonance at 445 nm (a), 560 nm (b) and 630 nm (c). The excitation wave is circularly polarized in the assembly plane, (d) Map of $\langle F_{ij}^2 \rangle$ the field intensity enhancement calculated at 560 nm and averaged over the gap distance between each pair of nanoparticles; (e) plot of $\langle F_{ij}^2 \rangle$ as a function of inter-particle distance l_{ij} .

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224 The $\langle F_{ij}^2 \rangle$ calculated using the DDA numerical simulations are used in Eq. 6 to 225 generate the local photoconductances. The complex admittance matrix [Y] of the electrical network, formed by the interconnected nano-junctions, is constructed assuming that all first neighbor nanoparticles are located within a ring centered on the considered nanoparticle. The current flowing throughout the NP network is computed according to Kirchhoff's laws and by solving numerically the matrix equation[32]:

231 Eq. 8 $[V(\omega)] = [Y(\omega)]^{-1}[I(\omega)]$

where $[\mathbf{V}(\boldsymbol{\omega})]$ and $[\mathbf{I}(\boldsymbol{\omega})]$ are, respectively, the voltage and the injected current vectors, and $[\mathbf{Y}(\boldsymbol{\omega})]$ is the complex admittance matrix of which non-diagonal and diagonal terms are, respectively, $\mathbf{Y}_{ij}(\boldsymbol{\omega}) = -\mathbf{\chi}_{ij}(\boldsymbol{\omega})$ for $i \neq j$ and $\mathbf{Y}_{ii}(\boldsymbol{\omega}) = \sum_{j} \mathbf{\chi}_{ij}(\boldsymbol{\omega})$; the latter being the total admittance connected to node *i* [33].

The overall admittance of the network is $Y_0^{-1}(\omega) = V_0(\omega)/I_0(\omega)$ where $V_0(\omega)$ is the voltage vector at the collecting electrode and $I_0(\omega)$ is the injected current vector.

It is important to note that after the admittance $\chi_{ij}(\omega)$ (Eq. 1) of the local nano-junction is adjusted for the local photo-conductance $g_{ij_photo}(\lambda)$ (Eq. 6), calculated using DDA simulations, and the matrix equation (Eq. 8) is numerically solved using Kirchhoff's laws, one obtains the overall conductance, capacitance, and photo-conductance of the nanoparticle assembly. The numerical simulations utilizing this strategy enable modeling of the plasmo-electronic properties of self-assembled metal nanoparticles and is, going forward, referred to as DDA-Kirchhoff's method.

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246 4. Results and discussion:

247 4.1 Numerical simulations:

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Figure 4 presents Nyquist plots (Figure 4a) and resonance curves of the imaginary part $-Z''(\omega)$ of the impedance calculated using DDA-Kirchhoff simulations. The parameters used in these simulations are $R_0 = 80 \text{ k}\Omega$ (in Eq. 2) and $k_0 = 18 \text{ nS.W}^{-1}$.cm² (in Eq. 7). The choice of these values will be discussed later.

All Nyquist plots have nearly a semicircle shape which is a characteristic feature of an equivalent circuit consisting in parallel resistance R, capacitor C and photo-resistance G_{photo}^{-1} .



\overline{257} Figure 4 : DDA-Kirchhoff numerical calculations of the impedance of the network shown in Figure ESI 1a. (a) impedance Nyquist plots in the range 20 Hz-1 MHz, without and with optical excitation at 532 nm with intensity increasing from 0 to $1W/cm^2$ (inset: normalized photoconductance as a function of normalized I_0). (b) Spectrum of the Imaginary part of the calculated impedance $-Z''(\omega)$ (inset: corresponding f_0 evolution as a function of laser intensity).

The frequency dependence of the impedance arises from the capacitance contribution only. At this step, R, C and G_{photo}^{-1} can be considered as mesoscopic quantities reflecting the electric and plasmo-electric properties of the 100 nm x 100 nm simulated network (Figure ESI 1a) formed by the interconnected nano-junctions. They are not macroscopic quantities yet, since the latter are related to the macroscopic properties of the samples (Figure 1) onto which impedance spectroscopy measurements were performed (see discussion below).

First, a clear decrease of the impedance with increasing intensity of the optical 269 excitation can be observed in Figure 4a. This can be understood in terms of the 270 equivalent circuit impedance $\frac{\tilde{R}}{1+RG_{photo}}$ formed by the parallel resistance and photo-271 resistance G_{photo}^{-1} in the low-frequency limit (values of $Z'(\omega)$ on the horizontal axis 272 of Nyquist plots in Figure 4a). Nyquist plot calculated without light irradiation 273 274 $(G_{photo} = 0)$, gives $R = 1.4 T\Omega$. With increasing optical excitation, G_{photo} increases and may dominate the resistive character of the circuit in the limit of strong irradiation 275 276 intensity $(G_{photo} \gg R)$. The inset of Figure 4a shows the values of G_{photo} deduced from the low-frequency limit of the Nyquist plots (Figure 4a). 277

278 Inset of Figure 4a shows that G_{photo} increases linearly from 0 to c.a. 0.4 pS with irradiation intensity I_0 in agreement with the local photo-conductance model (Eq. 279 280 6) implemented at the nanoscale and with the experimental data (Figure ESI 2). 281 Moreover, one can notice in Figure 4 that the Nyquist plots are not perfect semi-circles; 282 they are depressed, *i.e.* the ratio between the maximum values of the imaginary and real parts of the impedance $-Z''_{max}/Z'_{max} < 0.5$. For instance, without optical excitation (black dots in Figure 4a) $-\frac{Z''_{max}}{Z'_{max}} = 0.36$ This depressed feature suggests that the equivalent circuit is formed by a distribution of the figure 4. 283 284 that the equivalent circuit is formed by a distribution of parallel resistance and 285 capacitor circuits rather than being defined by a single circuit. Such a distribution is 286 287 generated by the disorder due to size and position fluctuations of the nanoparticles and 288 also to point defects and dislocations present in the assembly network (Figure 2a and Figure ESI 1a). Indeed, as shown in Figure ESI 4, for a perfectly ordered hexagonal 289 290 arrangement of the nanoparticles, the calculated Nyquist plot is a perfect semi-circle. When 15% random fluctuations of the nanoparticle size and position are introduced, 291 292 all the Nyquist plots calculated for the different random guesses, are not only depressed 293 but their shape clearly deviates from a semi-circle (Figure ESI 4). This occurs because of the fluctuations of the local inter-particle tunneling resistance R_{ij} , capacitor C_{ij} and 294 photo-conductance g_{ij_photo} which lead to statistical distributions of relaxation times 295 $\tau_{ij} = \frac{R_{ij}C_{ij}}{1 + R_{ij}g_{ij_photo}}$. As a matter of fact, in a perfectly ordered network, the interparticle 296 separation l_{ij} and hence R_{ij} , C_{ij} and $g_{ij_photo}^{-1}$ are well defined, thus leading to a 297 298 unique relaxation time τ_{ii} (Figure ESI 5b). Figure 4b shows the imaginary part -Z'' of the impedance as a function of 299 300

frequency. Each spectrum consists of a resonance peak. Assuming a perfectly ordered network, the $-Z''(\omega)$ resonance peak has a Lorentzian line shape (corresponding to a single relaxation time) and the resonance frequency is given by $f_0 = \frac{1}{2\pi RC}$; at the nanojunction scale f_0 is determined by the interparticle tunnelling resistance (Eq. 2) and capacitor (Eq. 5). In the numerical simulations, the tunnelling parameter R_0 = 305 80 k Ω has been chosen in such a way that the resonance frequency $f_0 = 28 \, kHz$ corresponds to the one observed experimentally (see discussion below), without 306 optical excitation, which leads to $R = 1.4 T\Omega$ and C = 4aF. This latter value is the 307 equivalent capacitor of all serie and parallel nano-junctions forming the electrical 308 network (C_{ij} being given by Eq. 5). The large value of R and the small value of C are 309 consistent with the small size of the model nanoparticle network (100 nm x 100 nm). 310 311 Under optical illumination, the resonance frequency increases with increasing light intensity (inset of Figure 4b). As a matter of fact, the resonance frequency of the 312 313 equivalent circuit shown in Figure 1b is given by:

$$F_0 = \frac{1 + RG_{photo}}{2\pi RC}$$

Hence, when G_{photo} increases, the resistive component of the equivalent 315 circuit decreases and the resonance frequency increases linearly with irradiation 316 intensity (inset of Figure 4b) in agreement with Eq. 6. The maximum of the resonance 317 peak also decreases for the same reason. 318

It is worth to underline that the line shape of the $-Z''(\omega)$ resonance peaks in 319 Figure 4b is not described by a Lorentzian function. Indeed, because of the disorder 320 321 effects discussed above, the resonance peaks in Figure 4b are inhomogenously broadened according to the statistical distributions of the local relaxation time τ_{ij} . To 322 confirm this point, we have calculated analytically the impedance Nyquist plot and 323 resonance peak starting from the distribution of the relaxation times of the model 324 nanoparticle network shown in Figure ESI 5. The depressed feature of the Nyquist plot 325 and the non Lorentzian shape of -Z'' resonance are well reproduced thus confirming 326 the role of disorder (Figure ESI 5). 327

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4.2 Plasmoelectronic conduction paths:

For a full understanding of the optical excitation effect on the charge transport 331 properties, it is interesting to exploit the numerical simulations in order to investigate 332 333 the conduction paths supported by the nanoparticle network. The length of a conducting path and its electric characteristics are extracted from the numerical 334 simulations as follows: first, the spatial distribution of all the nano-junctions formed 335 336 by each pair of first neighbor nanoparticles is constructed according to the positions of 337 the nanoparticles within the network. Second, only paths connecting the injection and 338 the collection electrodes are selected. These percolating paths are the ones directly involved in the impedance spectroscopy measurements. Then, the length L_k of each 339 340 individual k-path is calculated by summing the nano-junctions impedance. Its 341 admittance is given by:

342 Eq. 10:
$$Y_k = \frac{\prod_{n=1}^m \chi_{ij,n}}{\sum_{n=1}^m \prod_{p=1, n \neq p}^m \chi_{ij,p}}$$

where m is the number of nano-junctions along the k-path and χ_{ij} is a nano-junction 343 admittance (Eq. 1). 344

345 Figure 5 displays path length histograms calculated at the resonance frequency f_0 = 28 kHz of the nanoparticle network. Without optical excitation, the path length 346 347 histogram is bimodal with a main maximum around 220 nm, *i.e.*, nearly twice the interelectrode separation and a secondary maximum at longer paths between 300 and 400 348 nm. Under optical excitation at 1 W/cm², the distribution of path lengths is more 349

uniform: the path length histogram is Gaussian like centered around 250 nm with 100 nm half width at half maximum. The optical excitation has the effect of condensing the conduction path lengths around a mean value. This is related to the fact that the photo-resistance (Eq. 6) due to the hot charge carriers is less sensitive to disorder effects (*i.e.* to nanoparticle size and position fluctuations) than the resistance associated with thermalized charge carriers (see Figure ESI 6).

Figure 5 c-f depict the real (conductance) and imaginary (susceptance) parts of 356 path admittance as a function of path length calculated at the resonance frequency. For 357 a given path length, the values of the admittance are scattered over a wide range (Figure 358 5 c-f) which means that paths of the same length may have very different electrical 359 360 characteristics. This is particularly visible in the conductance (Figure 5c, d) because the tunnelling resistance varies exponentially with the inter-particle distance (Eq. 2) 361 362 and is therefore very sensitive to fluctuations of the size and position of a nanoparticle within the network. The susceptance of the nanoparticle network (Figure 5e, f) is less 363 sensitive to disorder effects because of the weaker logarithmic dependence of the local 364 365 capacitors (Eq. 5) on the interparticle distance.

As shown in Figure 5c, d path admittance is enhanced by the optical excitation 366 367 in agreement with Nyquist plots (Figure 4); as a consequence, for a given path length, the conductance and susceptance are scattered over a wider range (compared to Figure 368 369 5 e, f). The optical excitation has a strong impact on the conductance since the local photo-conductance introduced in Eq. 6 is purely real. For this same reason, we might 370 have expected no influence on the susceptance. However, since the complex 371 admittance combines both resistive and capacitive contributions (Eq. 10), its 372 373 susceptance component depends not only on the local interparticle resistance R_{ii} and local interparticle capacitor C_{ij} , but also on the local photo-resistance g_{ij_photo} ⁻¹. That's 374 why the susceptance of the nanoparticle network is also modified by the optical 375 excitation. The path admittance is strongly influenced by disorder as shown by the 376 scattered values of conductance and capacitance (Figure 5c-f) and decreases roughly 377 as the inverse path length. They are strictly proportional to the inverse path length only 378 379 in the case of a perfectly ordered network as shown in previous works [34].



380Figure 5: (a,b) histograms of conduction path lengths extracted from the DDA-Kirchhoff numerical simulations of the381TEM nanoparticle network shown in Figure ESI 1a. Calculations were performed at the resonance frequency $f_0=28$ 382kHz, without and with optical excitation at 560 nm wavelength and 1 W/cm² intensity. (c, d) path conductance as a383function of path length L_k . (e, f) path susceptance as a function of path length L_k . The insets in c-f show conductance384(c,d) and susceptance (e-f) histograms.

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Moreover, Figure 5 c-f display the conductance and susceptance histograms calculated with and without optical excitation. The histograms follow a log-normal distribution, as shown in a previous study [34], which indicates that conductance and susceptance indeed result from the sum of the numerous small independent local interparticle impedances along the conducting paths.



Figure 6: Plasmo-electronic conduction paths. (a) Conduction path A is calculated without optical excitation. (b, c 393 and d) Paths B, C and D are calculated with optical excitation at 532 nm and intensity from 0 to 1 W/cm². Each path 394 module admittance $|Y_k|$ is in the range $[1.8x10^{-14} \text{ S} - 2x10^{-14} \text{ S}]$. The path length decreases from 200 nm for path A to 395 197 nm for path F. 396

391 392

397 DDA-Kirchhoff numerical simulations allow to visualize the conduction paths and the changes induced by the optical excitation. To do so, we have selected 398 conduction paths with nearly the same conductance c.a. 2.10⁻¹⁴ S and comparable 399 length around 200 nm, *i.e.*, twice the network size and inter-electrodes separation. In 400 401 this way, when the optical excitation is applied, only the relative contribution of the 402 resistance and photo-resistance, along the path, is modified; its overall conductance 403 being nearly constant. Figure 6 displays such conduction paths without (path labeled 404 A) and with (paths labeled B-F) optical excitation. Without optical excitation, path A 405 involves 21 nano-particles and the average distance between the involved first 406 neighbor nanoparticles is 2.68 nm. With optical excitation at a moderate intensity of 407 0.2W/cm², path B is 198 nm long and involves 20 nanoparticles with a slightly larger average interparticle distance of 2.70 nm. When the optical excitation is increased to 408 0.4W/cm², path C involves 20 nanoparticles with an average distance of 2.74 nm. With 409 further increase from 0.6 to 1 W/cm², the length of path D, E and F are *c.a.* 197nm and 410 involves 20 nanoparticles with increasing average distances from 2.78 to 2.84 nm (see 411 Figure 7). The variation of the relative admittance $\Delta Y_k = (|Y_k| - |Y_k|_{dark})/|Y_k|_{dark})$ of the 412 413 conduction paths shown in Figure 6 is less than 5% which ensures the fact that we are 414 comparing conduction paths with very similar admittance.

415 It appears that the effect of the optical excitation is to reduce the path length and correlatively increase the average distance $\langle l_{ii} \rangle$ between first neighbor 416

417 nanoparticles for a given path admittance. We found that $\langle l_{ij} \rangle$ increases by *c.a.* 0.16 418 nm per unit of optical excitation intensity (in W⁻¹cm²) as shown in Figure 7.



419 420 Figure 7 : Average distance $\langle l_{ij} \rangle$ between first neighbor nanoparticles involved in the plasmoelectronic conduction 421 paths (A to F of Figure 6) as a function of laser intensity I_0 . The doted line shows a linear least-square fit.

422

423 This effect can be understood in terms of optical generation of hot carrier's. 424 Indeed, according to the local photo-conductivity (Eq. 6 and Eq. 7), the photo-excited hot carriers can tunnel over larger distances ($\beta^{-1} = 0.27 nm$) than thermalized 425 carriers ($\beta^{-1} = 0.2 nm$). Therefore, under optical excitation a smaller number of 426 nanoparticles is required for a conduction path with the same conductance compared 427 428 to the situation without optical excitation. This underlines the role of the plasmonic 429 resonance in terms of not only enhancement of the local optical field (Figure 3), but 430 also of photo-generation of hot carriers. This latter effect is at the origin of the different 431 optical conduction paths displayed in Figure 6 which we may call plasmo-electronic 432 conduction paths.

433

434 **4.3** Comparison between DDA-Kirchhoff simulations and experiments:

One must scale-up the dimensions of the simulated nanoparticle network to the 435 macroscopic scale in order to compare numerical simulations with impedance 436 spectroscopy data, quantitatively. However, numerical simulations of the charge 437 transport properties of a macroscopic nanoparticle network require a significant 438 439 amount of computation time and memory resources. To overcome this difficulty we 440 use a simple rescaling method: the 100 nm x 100 nm simulated network (Figure 1) is 441 replicated N_i times in series and N_i times in parallel; N_i and N_j are determined, 442 respectively, by the distance between the interdigitated electrodes (Figure 1) and by their length. Additionally, a series contact resistance R_S can be added to take into 443 account imperfections in the electrical connexion between the electrodes and the 444 445 nanoparticle network. Then, the macroscopic impedance is calculated simply as

446 Eq. 11
$$Z_{macro}(\omega) = R_s + \frac{1}{N_e} \cdot \frac{N_i}{N_j} \cdot Z(\omega)$$

447 where $Z(\omega)$ is the mesoscale impedance of the 100 nm x 100 nm nanoparticle 448 network calculated by DDA-Kirchhoff numerical simulations (Figure 3) and N_e is the 449 number of interdigited electrodes (Figure 1). In our device N_i =50; N_j =10000 and 450 N_e =50.

451 At high frequencies, the resistance of the nanoparticle network is shorted by its capacitance and only the series resistance R_s remains and can be estimated from the 452 experimental data. We found $R_s \leq 1k\Omega$ from the impedance measured at the highest reachable frequency (10 MHz in our case). It is worth to underline that, according to 453 454 Eq. 11, $-Z''_{macro}(\omega)$ and $-Z''(\omega)$ peaks exhibit the same resonance frequency f_0 and 455 line shape; they differ only in their magnitudes by the scaling factor $\frac{1}{N_e} \cdot \frac{N_i}{N_j}$. The 456 457 straightforward rescaling method (Eq. 11) assumes that the size of the mesoscale network is large enough to capture all the structural features of the nanoparticle 458 459 network, *i.e.*, the spatial arrangement of the nanoparticles including fluctuations of their sizes and positions as well as the presence of point defects and dislocations. 460

Figure 8 presents a comparison between the results of DDA-Kirchhoff's numerical simulations and impedance spectroscopy data.



463 Figure 8 : (a) Comparison between measured and calculated (full lines) impedance Nyquist's plots without and with 464 optical excitation at $\lambda = 405$, 532, 640 nm and 0.36 W/cm² intensity (b) corresponding spectra of $-Z''(\omega)$; the table 465 inserted in (a) shows the values of the $k_0(\lambda)$ factor in Eq. 6 used as a fitting parameter of the simulated Nyquist plots 466 to the measured ones.

467 In the numerical simulations there are two adjustable parameters: the 468 interparticle tunneling resistance R_0 in Eq. 2 and the charge carrier photo-generation 469 efficiency k_0 in Eq. 7 when the optical excitation is used. As mentioned above, $R_0 =$ 470 80 k Ω has been determined in such a way that the calculated resonance frequency $f_0 =$ 471 28 kHz coincides with the one observed in the impedance spectroscopy 472 measurements. Using this value of R_0 and the rescaling method described above one 473 obtains the macroscopic values $R \sim 140 M\Omega$ and $C \sim 0.04 pF$. At this point one expects a good matching between the rescaled impedance (Eq. 11) and the measured one. 474 475 However, we found that the calculations overestimate the measured impedance. The 476 latter is of the order of 2.5 M Ω as can be seen on the Nyquist's plot (horizontal axis of 477 Figure 8). The origin of this discrepancy lies in three main points:

First, the mesoscale network is assumed to be representative of the entire macroscopic network. However, Figure ESI 4 shows that for a 100 nm x 100 nm network with a hexagonal arrangement of the nanoparticles in which 15% size and position fluctuations are included, the impedance may vary up to a factor 20 depending on the network selected by the random guess (only a factor 4 is presented in Figure ESI 4). 484 Second, we found that depending on the filtering parameters used in the software 485 assisted filtering of the TEM image (Figure ESI 1a), the estimated nanoparticle size 486 position may vary by 5%. This variation, combined with the strong sensitivity of the tunneling resistance to the inter-particle distance (Eq. 2), leads to an uncertainty on the 487 488 calculated network impedance that may also reach an order of magnitude. Moreover, 489 the parameters β and E_C determine the interparticle tunneling resistance (Eq. 2) and 490 may be affected by conformational changes of the ligand molecules which in turn may have a strong impact on the overall macroscopic resistance. 491

Third, we did not take into account a possible effect of humidity from the
environment that would modify the conformation of the ligand molecules and thus the
permittivity of the medium surrounding the nanoparticles.

495 For these reasons, the calculated and measured impedances are significantly 496 different in magnitudes. However, the shape of the calculated and measured Nyquist diagrams and resonance peaks can be compared once their amplitudes adjusted. To do 497 that, the calculated low-frequency impedance is fitted to the measured one, in the 498 499 absence of optical excitation. This corresponds to the (black) dot on the right side 500 (horizontal axis) of the Nyquist plot in Figure 8a. As shown in Figure 8, the Nyquist plot, measured without optical excitation, is depressed $-Z''_{max}/Z'_{max} \sim 0.4$ (Figure 501 8a and Figure ESI 6) and the resonance peak of $-Z''(\omega)$ has a non-lorentzian shape 502 characterized by a low-frequency asymmetry. The calculations (full lines in Figure 8) 503 well account for these two features which are correlated and reflect the disorder effects 504 505 discussed in Figure 4. In fact, the measured and calculated linewidths of the resonance peaks in Figure 8b are comparable, hence indicating that the variations in the size and 506 location of the nanoparticles and the networks defects (disorientations, dislocations...) 507 (Figure 1) are quite representative of the disorder present at the macroscopic scale. 508

509 Let's now focus on the effect of the optical excitation. As shown in Figure 8, the nanoparticle assembly has been excited at 405, 532 and 640 nm wavelengths with 0.36 510 511 W/cm² laser intensity. The reduction in the radius of the Nyquist plots in Figure 8a and 512 in the amplitude of the resonance peaks in Figure 8b demonstrate that, after optical excitation, the measured impedance of the nanoparticle network is lowered due to a 513 514 photo-conductance contribution in agreement with the simulation results presented in 515 Figure 4. Remarkably, the largest photo-induced effect is observed for $\lambda = 532$ nm (green dots in Figure 8a), i.e., close to the plasmon resonance of the nanoparticle 516 network (Figure 2) which underlines the plasmo-electronic character of the photo-517 518 conductance.

519 DDA-Kirchhoff numerical simulations of the photo-induced plasmo-520 electronic effect were then performed using the photo-current factor $k_0(\lambda)$ in Eq. 7 as an adjustable parameter. The agreement between the calculated and measured 521 522 impedance Nyquist plots and resonance peaks, under optical excitation, is satisfactory. In particular, the depressed character (Figure 8a) of the Nyquist plots and the linewidth 523 524 of the resonance peaks (*Figure 8b*) are well reproduced. The $k_0(\lambda)$ best-fit values are quoted in Figure 8b. Close to the plasmonic resonance the photo-current conversion 525 factor is estimated at $k_0(532nm) = 18 \pm 4 nS.W^{-1}.cm^2$ which means that at 0.36 526 W/cm², for nearly touching particles, the inter-particle photo-conductance is around 50 527 528 nS.

529 It is worth to underline that using the values of the nanoscopic photo-530 conductance efficiency $k_0(\lambda)$ quoted in Figure 8a, the DDA-Kirchhoff numerical simulations are able to account for the measured macroscopic photo-conductance as a

532 function of both the optical excitation wavelength (Figure 8) and intensity (Figure 9).

- 533 Close to the plasmonic resonance ($\lambda = 532nm$), we found that the macroscopic photo-
- 534 conductance efficiency is $250 \pm 40 \text{ nS.W}^{-1}$.cm².
- 535



Figure 9 : Calculated (triangles) and measured (dots) macroscopic photoconductance G_{photo} as a function of laser intensity I_0 at the plasmonic resonance (λ =532nm). The experimental photoconductance is extracted from the lowfrequency impedance spectroscopy measurements performed under optical excitation (Figure 8). The dashed line shows the linear variation fit which gives a macroscopic photo-conductance efficiency of 250 ± 40 nS.W⁻¹.cm².

As mentioned above, $k_0(\lambda)$ in Eq. 6 accounts for the light absorption and for 542 the inter-particle charge transfer of the photo-generated charge carriers. The fact, that 543 544 $k_0(\lambda)$ is maximum at $\lambda = 532 nm$ has to do with the transition dipole between initial 545 and final states involved in the optical absorption process. As a matter of fact, gold has inter-band transitions between occupied d-orbital and unoccupied s-orbital states 546 547 (above the Fermi level) with a maximum absorption around 500 nm wavelength [35]. The inter-band transitions overlap with the plasmonic resonance which is responsible 548 for the decay of the surface plasmons into hot electron-hole pairs. Therefore, a 549 maximum efficiency of photo-carrier generation is expected at the plasmonic 550 resonance as observed in Figure 8. Moreover, hybridization between the metal 551 nanoparticle and the dodecanethiol electronic states takes place because of the strong 552 bonding of the thiol molecules with the metal surface. In that case, one may also expect 553 transitions from the occupied d-orbital states of the gold nanoparticle to the un-554 occupied states of the thiol molecule which may also contribute to $k_0(\lambda)$. The 555 hybridization of the molecule/nanoparticle electronic states still need to be modelled 556 557 using quantum mechanics and implemented into DDA-Kirchhoff numerical 558 simulations in order to fully account for the photo-induced effects in self-assembled 559 nanoparticle assemblies.

560

561 5. CONCLUSION

To summarize, we presented a theoretical investigation of the plasmoelectronic properties of self-assembled gold nanoparticle networks in conjunction with
impedance spectroscopy measurements. A photo-electric nano-junction model,
formed by first neighbor nanoparticles, was introduced as an elementary building

566 block of a mesoscopic electrical circuit; the latter was rescaled to allow comparison 567 with experiments performed at the macroscopic scale. Its electric properties 568 (resistance, capacitance, and photo-resistance) were obtained by incorporating electrodynamic calculations of the local optical properties, based on the DDA method, into 569 570 Kirchhoff's current-bias equations. An important feature of the theoretical modeling is 571 that the actual spatial sizes and relative positions of the nanoparticles within the selfassembly are taken into account as they determine the local resistance, capacitance and 572 573 photo-resistance. The charge carrier transport across the nanoparticle network was numerically simulated using the developed DDA-Kirchhoff combined approach, and 574 analyzed in terms of impedance Nyquist's plots and resonance properties. The effect 575 576 of structural disorder has been addressed because it is critical in understanding the shape of impedance Nyquist plots and resonance curves. The DDA-Kirchhoff 577 578 numerical simulations were used to determine the percolating conduction paths, their statistical distribution, and the effect of optical excitation. Our main findings are : (i) 579 the plasmonic assisted photo-conductance is responsible for a decrease of the network 580 admittance and impacts both its impedance and susceptance. (ii) the shapes of the 581 impedance Nyquist plot and resonance curve may strongly deviate from, respectively, 582 583 a semi-circle and a Lorentzian function because of inhomogeneous distribution of relaxation times induced by disorder effects. (iii) the histograms of length and 584 585 admittance of conductions paths depend on optical excitation intensity. The path impedance and susceptance decrease roughly as the inverse path length. (iv) using 586 quantitative comparison between DDA-Kirchhoff numerical simulations and 587 experimental impedance spectroscopy data, the local photo-conductance of a single 588 nano-junction, with nearly teaching nano-particles, is estimated at 18 ± 4 nS.W⁻¹.cm² 589 at the plasmonic resonance. (v) using a close inspection of plasmo-electronic 590 conduction paths, we found that the role of the plasmonic resonance is twofold : first 591 it is responsible for enhancement of the photo-conductance through increased local 592 optical field intensity. Second, the conversion of surface plasmons into photo-593 generated hot charge carriers allow for inter-particle tunneling over larger distances 594 595 than thermalized ones.

The approach developed in this work is generic and can be used to account for
the transduction of light into electrical current in composite materials once the local
electric characteristics of the charge transport are implemented in elementary junctions
forming an electrical network.

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608 CONFLICT OF INTEREST:

609 The authors declare no conflict of interest.

610

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611 DATA AVAILABILITY:

612 Data underlying the results presented in this paper are not publicly available at this time but may be 613 obtained from the authors upon reasonable request.

615 SUPPLEMENTARY MATERIAL:

616 Inter-nanoparticle distance histogram, Normalized measured photoconductance G_{photo}, Schematic of inter-617 particle energy alignment, Impact of the network dispersion on the depressed semi-circles, Distribution 618 of relaxation times in disordered nanoparticle networks, Impact of the laser irradiation on the depressed 619 semi-circles. 620

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